

AUTOSWITCHING POWER MULTIPLEXER

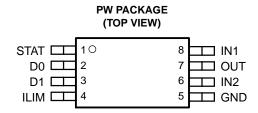
FEATURES

- Two-Input, One-Output Power Multiplexer With Low r_{DS(on)} Switches:
 - 84 m Ω Typ (TPS2115)
 - 120 m Ω Typ (TPS2114)
- Reverse and Cross-Conduction Blocking
- Wide Operating Voltage Range: 2.8 V to 5.5 V
- Low Standby Current: 0.5 µA Typical
- Low Operating Current: 55 μA Typical
- Adjustable Current Limit
- Controlled Output Voltage Transition Times, Limits Inrush Current and Minimizes Output Voltage Hold-Up Capacitance
- CMOS and TTL Compatible Control Inputs
- Manual and Auto-Switching Operating Modes
- Thermal Shutdown

• Available in a TSSOP-8 Package

APPLICATIONS

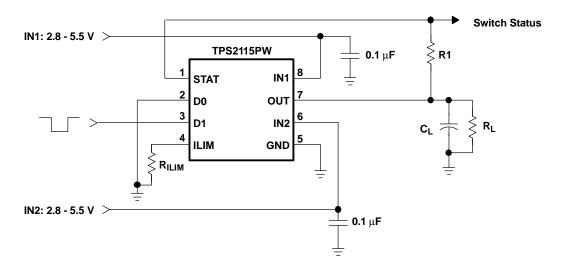
- PCs
- PDAs
- Digital Cameras
- Modems
- Cell phones
- Digital Radios
- MP3 Players



DESCRIPTION

The TPS211x family of power multiplexers enables seamless transition between two power supplies, such as a battery and a wall adapter, each operating at 2.8-5.5 V and delivering up to 1 A. The TPS211x family includes extensive protection circuitry, including user-programmable current limiting, thermal protection, inrush current control, seamless supply transition, cross-conduction blocking, and reverse-conduction blocking. These features greatly simplify designing power multiplexer applications.

TYPICAL APPLICATION





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

FEATURE		TPS2110	TPS2111	TPS2112	TPS2113	TPS2114	TPS2115
Current limit adjustment range		0.31-0.75A	0.63-1.25A	0.31-0.75A	0.63-1.25A	0.31-0.75A	0.63-1.25A
0 11 1	Manual	Yes	Yes	No	No	Yes	Yes
Switching modes	Automatic	Yes	Yes	Yes	Yes	Yes	Yes
Switch status output		No	No	Yes	Yes	Yes	Yes
Package		TSSOP-8	TSSOP-8	TSSOP-8	TSSOP-8	TSSOP-8	TSSOP-8

ORDERING INFORMATION

T _A	PACKAGE	ORDERING NUMBER (1)	MARKINGS
-40°C to 85°C	TSSOD 8 (DM/)	TPS2114PW	2114
-40 C to 65 C	TSSOP-8 (PW)	TPS2115PW	2115

⁽¹⁾ The PW package is available taped and reeled. Add an R suffix to the device type (e.g., TPS2114PWR) to indicate tape and reel.

PACKAGE DISSIPATION RATINGS

PACKAGE	DERATING FACTOR	T _A ≤ 25°C	T _A = 70°C	T _A = 85°C
	ABOVE T _A = 25°C	POWER RATING	POWER RATING	POWER RATING
TSSOP-8 (PW)	3.87 mW/°C	386.84 mW	212.76 mW	154.73 mW

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

			TPS2114, TPS2115
VI	Input voltage range	IN1, IN2, D0, D1, ILIM ⁽²⁾	-0.3 V to 6 V
Vo	Output voltage range ⁽²⁾	OUT, STAT	-0.3 V to 6 V
Io	Output sink current	STAT	5 mA
	Continuous output ourrent	TPS2114	0.9 A
'o	Continuous output current	TPS2115	1.5 A
	Continuous total power diss	pation	See Dissipation Rating Table
T_J	Operating virtual junction ter	mperature range	-40°C to 125°C
T _{stg}	Storage temperature range		-65°C to 150°C
	Lead temperature soldering	1,6 mm (1/16 inch) from case for 10 seconds	260°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to GND.



RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
	Input voltage at INI4	V _{I(IN2)} ≥ 2.8 V	1.5	5.5	V
V _I Input voltage at IN1	V _{I(IN2)} < 2.8 V	2.8	5.5	V	
\/	Input voltage at INO	$V_{I(IN1)} \ge 2.8 \text{ V}$	1.5	5.5	V
V _I	Input voltage at IN2	V _{I(IN1)} < 2.8 V	2.8	5.5	V
V _I	Input voltage at D0, D1	•	0	5.5	V
	Comment limit a diverter and many	TPS2114	0.31	0.75	^
O(OUT) Current limit adjustment range		TPS2115	0.63	1.25	Α
T _J	Operating virtual junction temperatu	re	-40	125	°C

ELECTROSTATIC DISCHARGE (ESD) PROTECTION

	MIN MAX	UNIT
Human body model	2	kV
CDM	500	V

ELECTRICAL CHARACTERISTICS

over recommended operating junction temperature range, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, $R_{(ILIM)} = 400 \Omega$ (unless otherwise noted)

-	PARAMETER	TEST CO	TPS2114			4	TF	5	UNIT	
PARAMETER		IESI CC	TEST CONDITIONS		TYP	MAX	MIN	TYP	MAX	UNIT
POWER S	SWITCH									
			$V_{I(IN1)} = V_{I(IN2)} = 5.0 \text{ V}$		120	140		84	110	
		$T_J = 25^{\circ}C$, $I_I = 500 \text{ mA}$	$V_{I(IN1)} = V_{I(IN2)} = 3.3 \text{ V}$		120	140		84	110	$m\Omega$
r (1)	Drain-source on-state	1[= 000 11#1	$V_{I(IN1)} = V_{I(IN2)} = 2.8 \text{ V}$		120	140		84	110	
r _{DS(on)} ⁽¹⁾	resistance (INx-OUT)		$V_{I(IN1)} = V_{I(IN2)} = 5.0 \text{ V}$			220			150	
	$T_J = 125^{\circ}C$, $I_I = 500 \text{ mA}$	$V_{I(IN1)} = V_{I(IN2)} = 3.3 \text{ V}$			220			150	$m\Omega$	
			$V_{I(IN1)} = V_{I(IN2)} = 2.8 \text{ V}$			220		-	150	

⁽¹⁾ The TPS211x can switch a voltage as low as 1.5 V as long as there is a minimum of 2.8 V at one of the input power pins. In this specific case, the lower supply voltge has no effect on the IN1 and IN2 switch on-resistances.



ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

ь	ADAMETED	TEST CONDITIONS	Т	PS211	5	UNIT	
Г	ARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
LOGIC INPUTS (D0 /	AND D1)						
V _{IH} High-lev	el input voltage		2			V	
V _{IL} Low-leve	el input voltage				0.7	V	
Input ou	rrent at D0 or D1	D0 or D1 = High, sink current			1	μΑ	
input cui	nent at bo of bi	D0 or D1 = Low, source current	0.5	1.4	5	μΑ	
SUPPLY AND LEAK	AGE CURRENTS						
		D1 = High, D0 = Low (IN1 active), $V_{I(IN1)}$ = 5.5 V, $V_{I(IN2)}$ = 3.3 V, $I_{O(OUT)}$ = 0 A		55	90		
Supply current from IN	VII (operating)	D1 = High, D0 = Low (IN1 active), $V_{I(IN2)}$ = 3.3 V, $V_{I(IN2)}$ = 5.5 V, $I_{O(OUT)}$ = 0 A		1	12		
Supply current from It	vi (operating)	D0 = D1 = Low (IN2 active), $V_{I(IN2)} = 5.5 \text{ V}$, $V_{I(IN2)} = 3.3 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			75	μA	
		D0 = D1 = Low (IN2 active), $V_{I(IN1)} = 3.3 \text{ V}$, $V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			1		
		D1 = High, D0 = Low (IN1 active), $V_{I(IN1)} = 5.5 \text{ V}$, $V_{I(IN2)} = 3.3 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			1		
Complete assessment from the	10 (an aratina)	D1 = High, D0 = Low (IN1 active), $V_{I(IN1)} = 3.3 \text{ V}$, $V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			75		
Supply current from IN2 (operating)		D0 = D1 = Low (IN2 active), $V_{I(IN1)} = 5.5 \text{ V}$, $V_{I(IN2)} = 3.3 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$		1	12	μA	
		D0 = D1 = Low (IN2 active), $V_{I(IN1)} = 3.3 \text{ V}$, $V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$		55	90		
Ouisseent surrent from	~ INIA (CTANIDDV)	D0 = D1 = High (inactive), $V_{I(IN1)}$ = 5.5 V, $V_{I(IN2)}$ = 3.3 V, $I_{O(OUT)}$ = 0 A		0.5	2		
Quiescent current from	II INT (STANDBY)	D0 = D1 = High (inactive), $V_{I(IN1)} = 3.3 \text{ V}$, $V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			1	μA	
Quiescent current from	~ IND (STANDDV)	D0 = D1 = High (inactive), $V_{I(IN1)} = 5.5 \text{ V}$, $V_{I(IN2)} = 3.3 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$			1	μA	
Quiescent current noi	ITINZ (STANDBT)	D0 = D1 = High (inactive), $V_{I(IN1)}$ = 3.3 V, $V_{I(IN2)}$ = 5.5 V, $I_{O(OUT)}$ = 0 A		0.5	2	μΑ	
Forward leakage curre (measured from OUT		D0 = D1 = High (inactive), $V_{I(IN1)}$ = 5.5 V, IN2 open, $V_{O(OUT)}$ = 0 V (shorted), T_J = 25°C		0.1	5	μΑ	
Forward leakage curre (measured from OUT		D0 = D1= High (inactive), $V_{I(IN2)}$ = 5.5 V, IN1 open, $V_{O(OUT)}$ = 0 V (shorted), T_J = 25°C		0.1	5	μΑ	
Reverse leakage curre (measured from INx to		D0 = D1 = High (inactive), $V_{I(INx)} = 0 V$, $V_{O(OUT)} = 5.5 V$, $T_J = 25^{\circ}C$		0.3	5	μΑ	
CURRENT LIMIT CIR	CUIT						
	TPS2114	$R_{(ILIM)} = 400 \Omega$	0.51	0.63	0.80		
Current limit		$R_{(ILIM)} = 700 \Omega$	0.30	0.36	0.50	_	
accuracy		$R_{(ILIM)} = 400 \Omega$	0.95	1.25	1.56	6 A	
	TPS2115	$R_{(ILIM)} = 700 \Omega$	0.47	0.71	0.99		
t _d Current	limit settling time ⁽¹⁾	Time for short-circuit output current to settle within 10% of its steady state value.		1		ms	
Input cu	rrent at ILIM	$V_{I(ILIM)} = 0 \text{ V}, I_{O(OUT)} = 0 \text{ A}$	-15		0	μA	

⁽¹⁾ Not tested in production.



over operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST COMPITIONS	Т	PS211	5	ш
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
UNDERVOLTAGE LOCKOUT	•	•			
IN1 and IN2 UVLO	Falling edge	1.15	1.25		V
	Rising edge		1.30	1.35	ľ
IN1 and IN2 UVLO hysteresis ⁽²⁾		30	57	65	mV
Internal \/ LIVI O (the higher of INI1 and INI2)	Falling edge	24	2.53		V
Internal V _{DD} UVLO (the higher of IN1 and IN2)	Rising edge		2.58	2.8	ľ
Internal V _{DD} UVLO hysteresis ⁽²⁾		30	50	75	mV
UVLO deglitch for IN1, IN2 ⁽²⁾	Falling edge		110		μs
REVERSE CONDUCTION BLOCKING					
$\Delta V_{O(I_block)} \qquad \begin{array}{l} \text{Minimum output-to-input voltage} \\ \text{difference to block switching} \end{array}$	D0 = D1 = high, $V_{I(INx)}$ = 3.3 V. Connect OUT to a 5 V supply through a series 1-k Ω resistor. Let D0 = low. Slowly decrease the supply voltage until OUT connects to IN1.	80	100	120	mV
THERMAL SHUTDOWN					
Thermal shutdown threshold ⁽²⁾	TPS211x is in current limit.	135			
Recovery from thermal shutdown ⁽²⁾	TPS211x is in current limit.	125			°C
Hysteresis ⁽²⁾			10		
IN2-IN1 COMPARATORS					
Hysteresis of IN2-IN1 comparator		0.1		0.2	V
Deglitch of IN2-IN1 comparator, (both↑↓) ⁽²⁾		90	150	220	μs
STAT OUTPUT					
Leakage current	V _{O(STAT)} = 5.5 V		0.01	1	μA
Saturation voltage	I _{I(STAT)} = 2 mA, IN1 switch is on		0.13	0.4	V
Deglitch time (falling edge only)			150		μs

⁽²⁾ Not tested in production.



SWITCHING CHARACTERISTICS

over recommended operating junction temperature range, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, $R_{(ILIM)} = 400 \Omega$ (unless otherwise noted)

	DADAMETED	TEOT 001	NDITIONS	-	ΓPS211	4	Т	PS211	5	
	PARAMETER	IESI COI	NDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
POWE	R SWITCH			•						
t _r	Output rise time from an enable (1)	$V_{I(IN1)} = V_{I(IN2)} = 5 \text{ V}$	$T_J = 25^{\circ}C$, $C_L = 1 \mu F$, $I_L = 500 \text{ mA}$, See Figure 1(a)	0.5	1.0	1.5	1	1.8	3	ms
t _f	Output fall time from a disable (1)	V _{I(IN1)} = V _{I(IN2)} = 5 V	$T_J = 25^{\circ}C$, $C_L = 1 \mu F$, $I_L = 500 \text{ mA}$, See Figure 1(a)	0.35	0.5	0.7	0.5	1	2	ms
		IN1 to IN2 transition, $V_{I(IN1)} = 3.3 \text{ V},$ $V_{I(IN2)} = 5 \text{ V}$	T_J = 125°C, C_L = 10 μ F, I_L = 500 mA [Measure		40	60		40	60	
t _t	Transition time ⁽¹⁾	IN2 to IN1 transition, $V_{I(IN1)} = 5 \text{ V},$ $V_{I(IN2)} = 3.3 \text{ V}$	transition time as 10-90% rise time or from 3.4 V to 4.8 V on V _{O(OUT)}], See Figure 1(b)		40	60		40	60	μs
t _{PLH1}	Turnon propagation delay from enable ⁽¹⁾	$V_{I(IN1)}=V_{I(IN2)}=5$ V, Measured from enable to 10% of $V_{O(OUT)}$	$T_J = 25^{\circ}C,$ $C_L = 10 \ \mu\text{F},$ $I_L = 500 \ \text{mA},$ SeeFigure 1(a)		0.5			1		ms
t _{PHL1}	Turnoff propagation delay from a disable ⁽¹⁾	$\begin{aligned} & V_{I(IN1)} = V_{I(IN2)} = 5 \text{ V}, \\ & \text{Measured from disable} \\ & \text{to 90\% of } V_{O(OUT)} \end{aligned}$	$\begin{split} T_J &= 25^{\circ}\text{C},\\ C_L &= 10~\mu\text{F},\\ I_L &= 500~\text{mA},\\ \text{See Figure 1(a)} \end{split}$		3			5		ms
t _{PLH2}	Switch-over rising propagation delay ⁽¹⁾	Logic 1 to Logic 0 transition on D1, $V_{I(IN1)} = 1.5 \text{ V}, \\ V_{I(IN2)} = 5 \text{ V}, \\ V_{I(D0)} = 0 \text{ V}, \\ \text{Measured from D1 to} \\ 10\% \text{ of } V_{O(OUT)}$	$T_J = 25^{\circ}C,$ $C_L = 10 \ \mu\text{F},$ $I_L = 500 \ \text{mA},$ See Figure 1(c)		0.17	1		0.17	1	ms
t _{PHL2}	Switch-over falling propagation delay ⁽¹⁾	Logic 0 to Logic 1 transition on D1, $V_{I(IN1)} = 1.5 \text{ V}, \\ V_{I(IN2)} = 5 \text{ V}, \\ V_{I(D0)} = 0 \text{ V}, \text{ Measured from D1 to 90% of } \\ V_{O(OUT)}$	$T_J = 25^{\circ}C,$ $C_L = 10 \ \mu\text{F},$ $I_L = 500 \ \text{mA},$ See Figure 1(c)	2	3	10	2	5	10	ms

(1) Not tested in production.

TRUTH TABLE

D1	D0	$V_{I(IN2)} > V_{I(IN1)}$	STAT	OUT ⁽¹⁾
0	0	X	Hi-Z	IN2
0	1	No	0	IN1
0	1	Yes	Hi-Z	IN2
1	0	X	0	IN1
1	1	X	0	Hi-Z

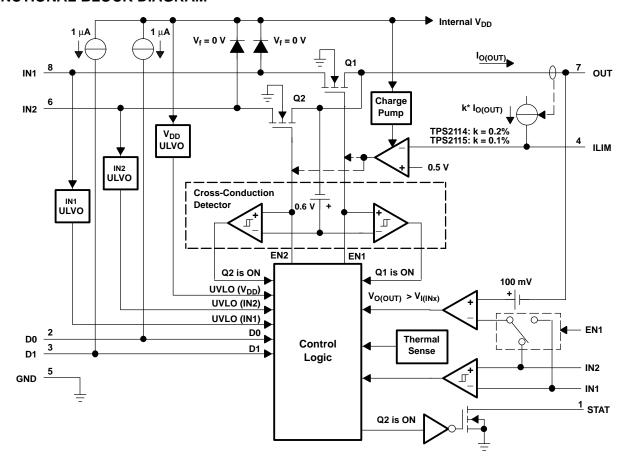
(1) The under-voltage lockout circuit causes the output OUT to go Hi-Z if the selected power supply does not exceed the IN1/IN2 UVLO, or if neither of the supplies exceeds the internal V_{DD} UVLO.



Terminal Functions

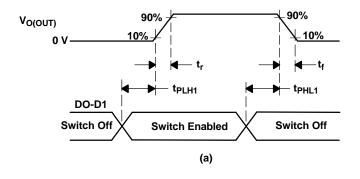
TERMI	INAL	I/O	DESCRIPTION
NAME	NO.	10	DESCRIPTION
D0	2	ı	TTL and CMOS compatible input pins. Each pin has a 1-µA pullup resistor. The truth table shown above illustrates
D1	3	I	the functionality of D0 and D1.
GND	5	I	Ground
IN1	8	I	Primary power switch input. The IN1 switch can be enabled only if the IN1 supply is above the UVLO threshold and at least one supply exceeds the internal V _{DD} UVLO.
IN2	6	I	Secondary power switch input. The IN2 switch can be enabled only if the IN2 supply is above the UVLO threshold and at least one supply exceeds the internal V _{DD} UVLO.
ILIM	4	I	A resistor $R_{(ILIM)}$ from ILIM to GND sets the current limit I_L to 250/ $R_{(ILIM)}$ and 500/ $R_{(ILIM)}$ for the TPS2114 and TPS2115, respectively.
OUT	7	0	Power switch output
STAT	1	0	STAT is an open-drain output that is Hi-Z if the IN2 switch is ON. STAT pulls low if the IN1 switch is ON or if OUT is Hi-Z (i.e., EN is equal to logic 0).

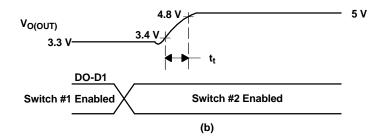
FUNCTIONAL BLOCK DIAGRAM





PARAMETER MEASUREMENT INFORMATION





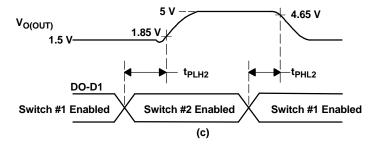
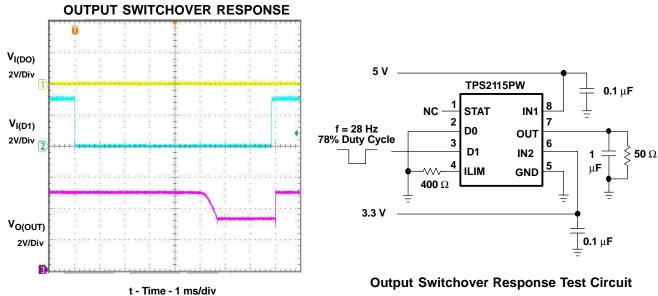


Figure 1. Propagation Delays and Transition Timing Waveforms

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TYPICAL CHARACTERISTICS



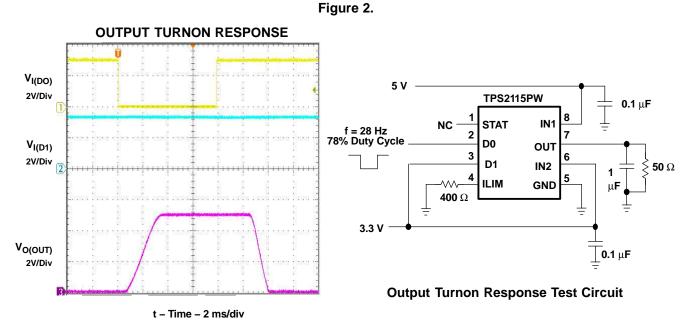


Figure 3.



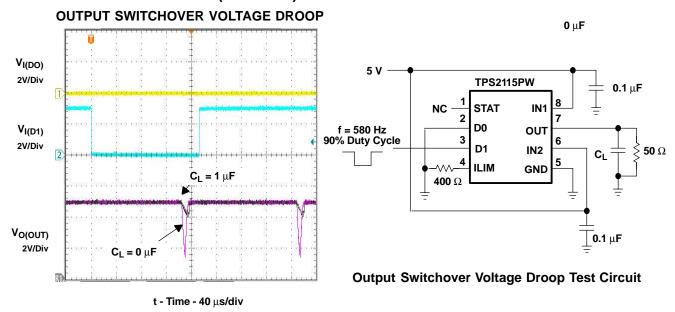
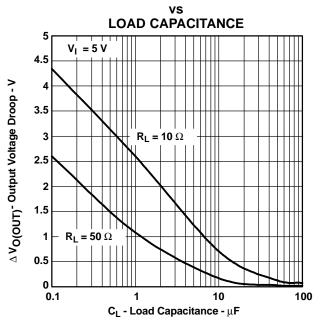
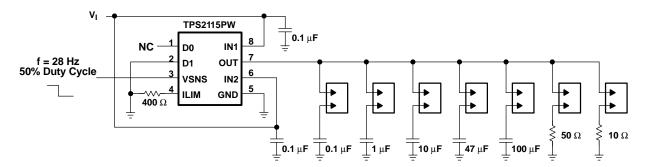


Figure 4.



OUTPUT SWITCHOVER VOLTAGE DROOP



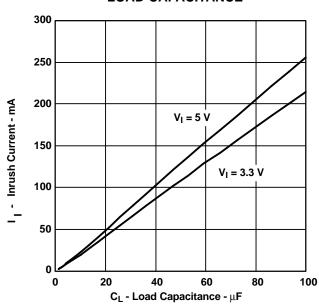


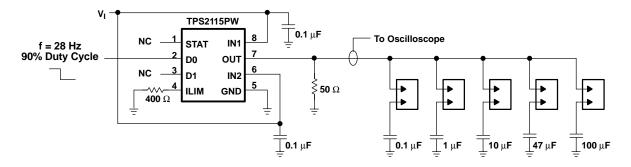
Output Switchover Voltage Droop Test Circuit

Figure 5.



INRUSH CURRENT vs LOAD CAPACITANCE





Output Capacitor Inrush Current Test Circuit

Figure 6.



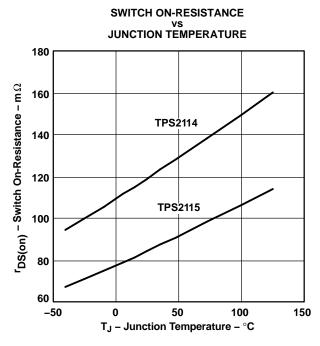
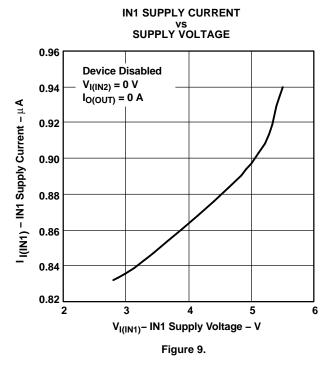
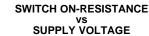
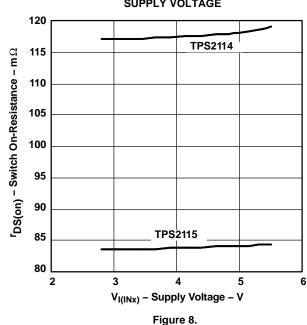


Figure 7.







IN1 SUPPLY CURRENT vs SUPPLY VOLTAGE

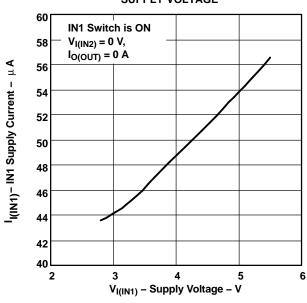
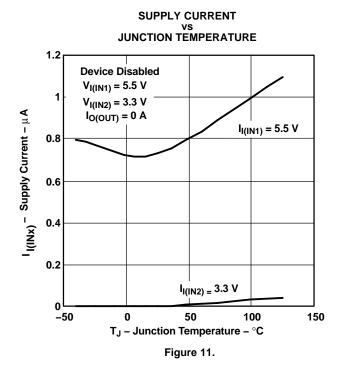


Figure 10.





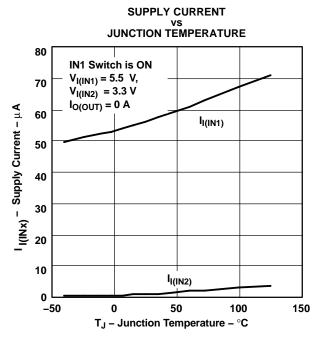


Figure 12.



APPLICATION INFORMATION

The circuit in Figure 13 allows one or two battery packs to power a system. Two battery packs allow a longer run time. The TPS2114/5 cycles between the battery packs until both packs are drained.

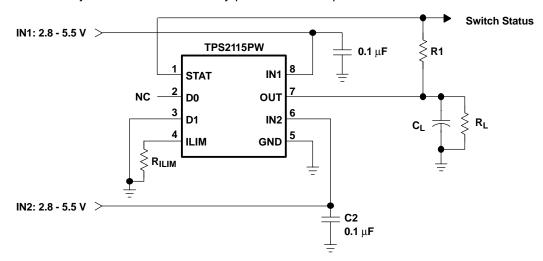


Figure 13. Running a System From Two Battery Packs

In Figure 14, the multiplexer selects between two power supplies based upon the D1 logic signal. OUT connects to IN1 if D1 is logic 1, otherwise OUT connects to IN2. The logic thresholds for the D1 terminal are compatible with both TTL and CMOS logic.

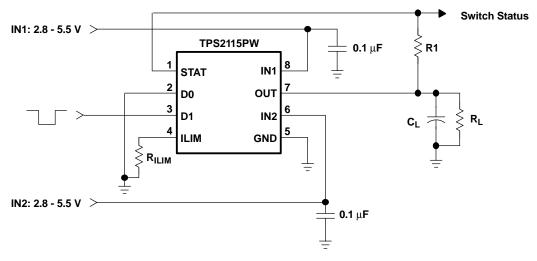


Figure 14. Manually Switching Power Sources



DETAILED DESCRIPTION

AUTO-SWITCHING MODE

D0 equal to logic 1 and D1 equal to logic 0 selects the auto-switching mode. In this mode, OUT connects to the higher of IN1 and IN2.

MANUAL SWITCHING MODE

D0 equal to logic 0 selects the manual-switching mode. In this mode, OUT connects to IN1 if D1 is equal to logic 1, otherwise OUT connects to IN2.

N-CHANNEL MOSFETs

Two internal high-side power MOSFETs implement a single-pole double-throw (SPDT) switch. Digital logic selects the IN1 switch, IN2 switch, or no switch (Hi-Z state). The MOSFETs have no parallel diodes so output-to-input current cannot flow when the FET is off. An integrated comparator prevents turnon of a FET switch if the output voltage is greater than the input voltage.

CROSS-CONDUCTION BLOCKING

The switching circuitry ensures that both power switches never conduct at the same time. A comparator monitors the gate-to-source voltage of each power FET and allows a FET to turn on only if the gate-to-source voltage of the other FET is below the turnon threshold voltage.

REVERSE-CONDUCTION BLOCKING

When the TPS211x switches from a higher-voltage supply to a lower-voltage supply, current can potentially flow back from the load capacitor into the lower-voltage supply. To minimize such reverse conduction, the TPS211x does not connect a supply to the output until the output voltage has fallen to within 100 mV of the supply voltage. Once a supply has been connected to the output, it remains connected regardless of output voltage.

CHARGE PUMP

The higher of supplies IN1 and IN2 powers the internal charge pump. The charge pump provides power to the current limit amplifier and allows the output FET gate voltage to be higher than the IN1 and IN2 supply voltages. A gate voltage that is higher than the source voltage is necessary to turn on the N-channel FET.

CURRENT LIMITING

A resistor $R_{(ILIM)}$ from ILIM to GND sets the current limit to 250/ $R_{(ILIM)}$ and 500/ $R_{(ILIM)}$ for the TPS2114 and TPS2115, respectively. Setting resistor $R_{(ILIM)}$ equal to zero is not recommended as that disables current limiting.

OUTPUT VOLTAGE SLEW-RATE CONTROL

The TPS2114/5 slews the output voltage at a slow rate when OUT switches to IN1 or IN2 from the Hi-Z state (see *Truth Table*). A slow slew rate limits the inrush current into the load capacitor. High inrush currents can adversely effect the voltage bus and cause a system to hang up or reset. It can also cause reliability issues—like pit the connector power contacts, when hot plugging a load like a PCI card. The TPS2114/5 slews the output voltage at a much faster rate when OUT switches between IN1 and IN2. The fast rate minimizes the output voltage droop and reduces the output voltage hold-up capacitance requirement.

www.ti.com 14-Oct-2022

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TPS2114PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2114	Samples
TPS2115PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2115	Samples
TPS2115PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2115	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

www.ti.com 14-Oct-2022

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 9-Aug-2022

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2115PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

www.ti.com 9-Aug-2022



*All dimensions are nominal

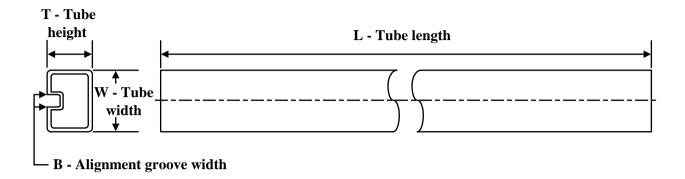
	Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
Г	TPS2115PWR	TSSOP	PW	8	2000	356.0	356.0	35.0	





www.ti.com 9-Aug-2022

TUBE

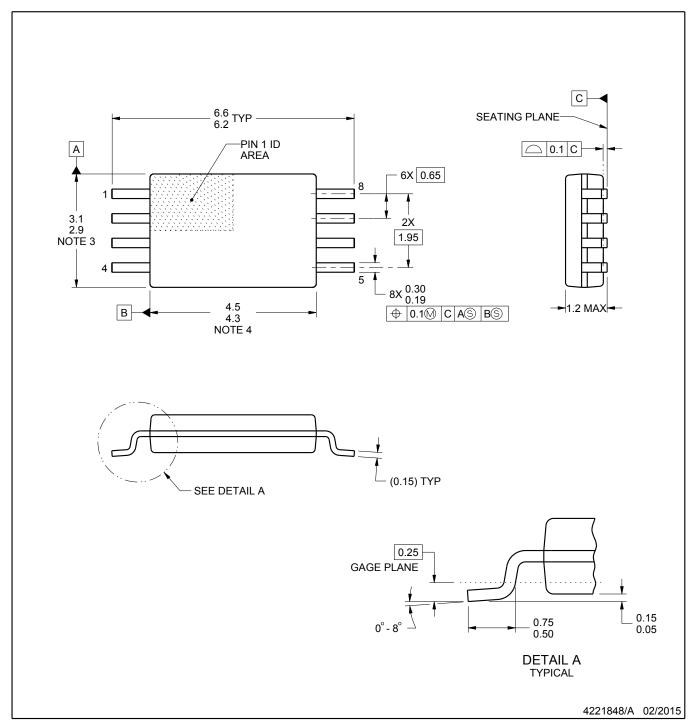


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS2114PW	PW	TSSOP	8	150	530	10.2	3600	3.5
TPS2115PW	PW	TSSOP	8	150	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



NOTES:

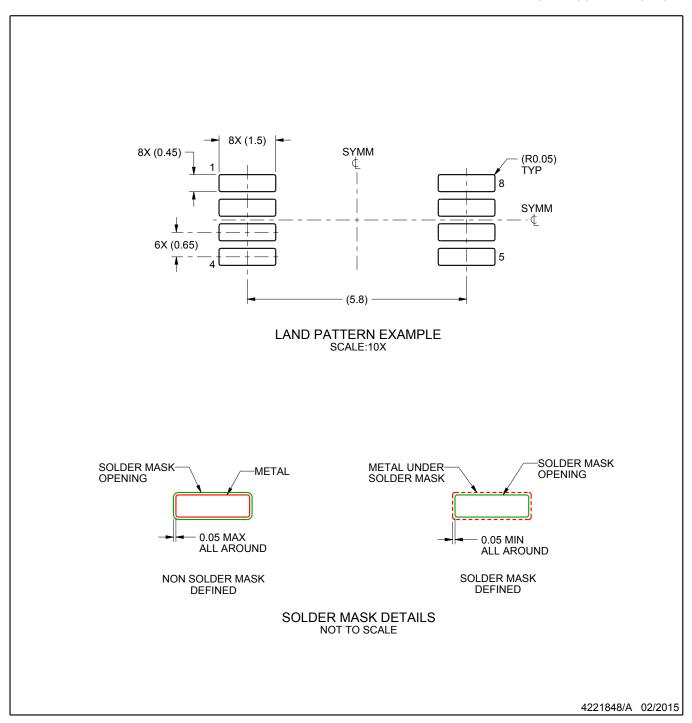
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE

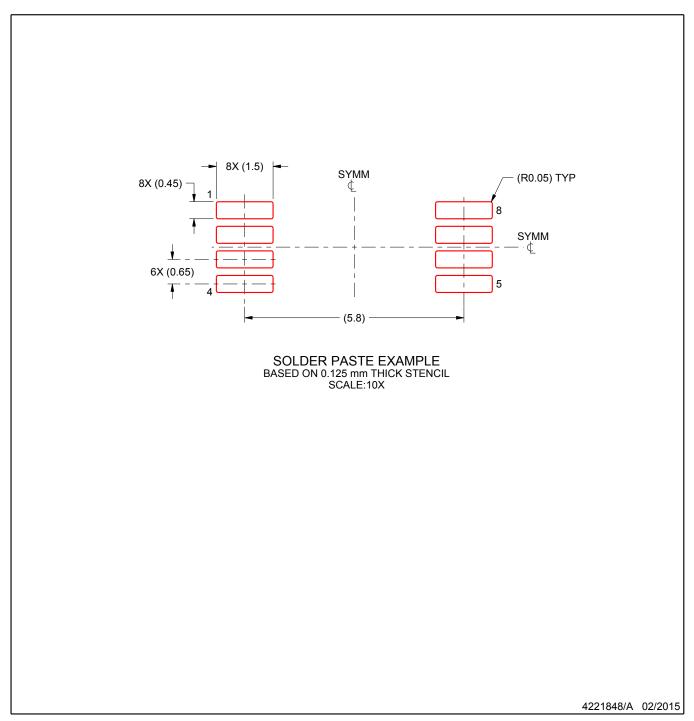


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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